

2SC4898

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Silicon NPN triple diffusion planar type

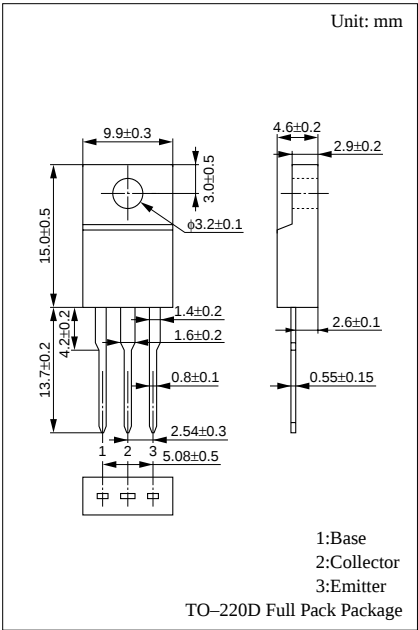
For high breakdown voltage high-speed switching

Features

- High-speed switching
- High collector to base voltage V_{CBO}
- Low collector to emitter saturation voltage $V_{CE(sat)}$

Absolute Maximum Ratings ($T_C=25^{\circ}C$)

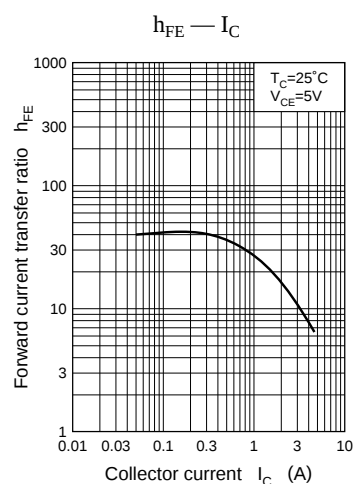
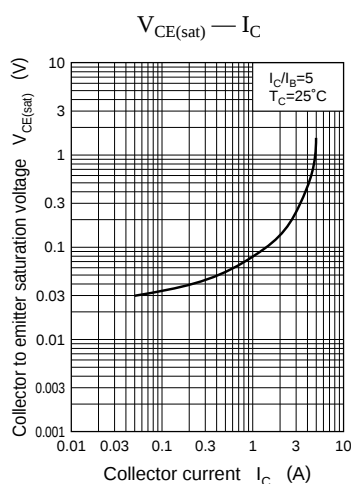
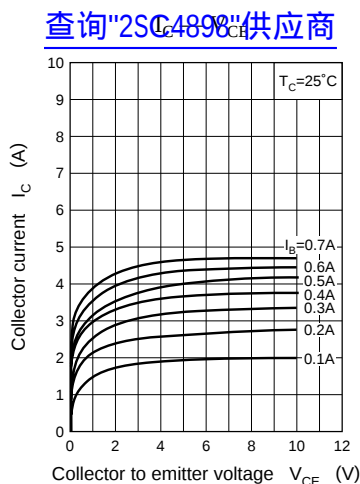
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	1000	V
Collector to emitter voltage	V_{CEO}	500	V
Peak collector current	I_{CP}	10	A
Collector current	I_C	5	A
Collector power dissipation	P_C	40	W
		2	
Junction temperature	T_j	150	$^{\circ}C$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}C$



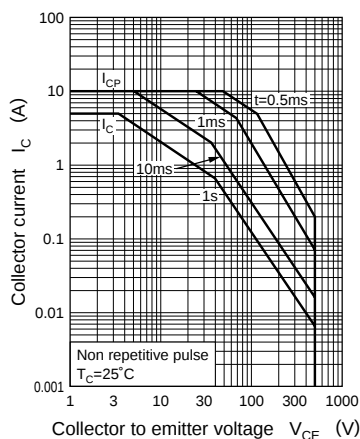
Electrical Characteristics ($T_C=25^{\circ}C$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 1000V, I_E = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 9V, I_C = 0$			100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 5V, I_C = 1A$	20		40	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 3A, I_B = 0.6A$			1	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 0.5A, f = 1MHz$		8		MHz
Turn-on time	t_{on}	$I_C = 3A, I_{B1} = 0.6A, I_{B2} = -0.6A, V_{CC} = 250V$			1.5	μs
Storage time	t_{stg}				3	μs
Fall time	t_f				1.0	μs

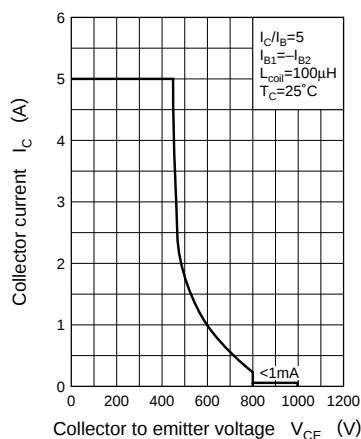
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Area of safe operation (ASO)



Area of safe operation, reverse bias ASO



$R_{th(t)} - t$

